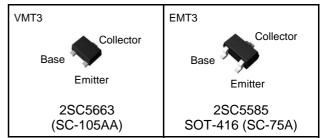
Datasheet



NPN 500mA 12V Low Frequency Amplifier Transistors

Parameter	Value
V_{CEO}	12V
I _C	500mA

Outline



Features

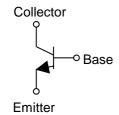
- 1) A Collector current is large. General Purpose.
- 2) Collector saturation voltage is low.

 $V_{CE(sat)} \le 250 mV$

At $I_C=200$ mA, $I_B=10$ mA

- 3) Complementary NPN Types: 2SA2030 (VMT3) / 2SA2018 (EMT3) / 2SA2119K (SMT3)
- 4) Lead Free/RoHS Compliant.

•Inner circuit



Applications

Switching circuit, Muting circuit

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SC5663	VMT3	1212	T2L	180	8	8,000	ВХ
2SC5585	EMT3	1616	TL	180	8	3,000	ВХ

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Values	Unit
Collector-base voltage	V _{CBO}	15	V
Collector-emitter voltage	V _{CEO}	12	V
Emitter-base voltage	V_{EBO}	6	V
Callegae august	I _C	500	mA
Collector current	I _{CP} *1	1	Α
Power dissipation	P _D *2	150	mW
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

●Electrical characteristics(Ta = 25°C)

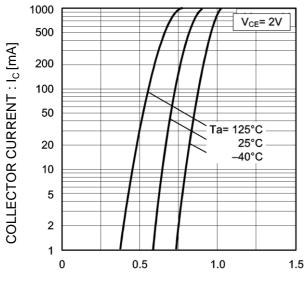
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	12	ı	-	V
Collector-base breakdown voltage	BV _{CBO}	I _C = 10μA	15	ı	-	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = 10μA	6	ı	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 15V	-	1	100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 6V	-	-	100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 200 \text{mA}, I_B = 10 \text{mA}$	-	90	250	mV
DC current gain	h _{FE}	$V_{CE} = 2V, I_{C} = 10mA$	270	ı	680	-
Transition frequency	f⊤	$V_{CE} = 2V$, $I_E = -10$ mA $f=100$ MH $_Z$	-	320	-	MHz
Output capacitance	Cob	$V_{CB} = 10V$, $I_E = 0mA$, $f = 1MHz$	-	7.5	-	pF

^{*1} P_W=10ms Single pulse.

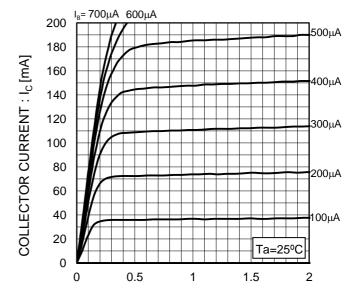
^{*2} Each terminal mounted on a reference footprint

●Electrical characteristic curves(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics Fig.2 Typical Output Characteristics

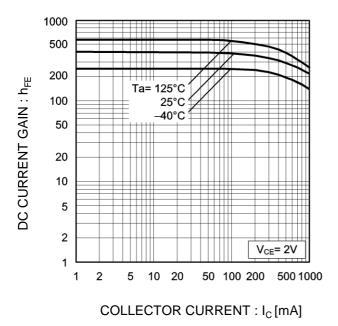


BASE TO EMITTER VOLTAGE : V_{BE} [V]



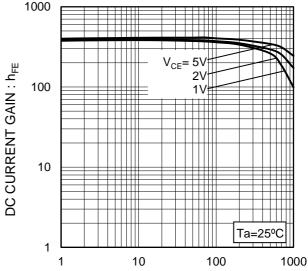
COLECTOR TO EMITTE VOLTAGE : $V_{CE}[V]$

Fig.3 DC Current Gain vs. Collector Current(I)



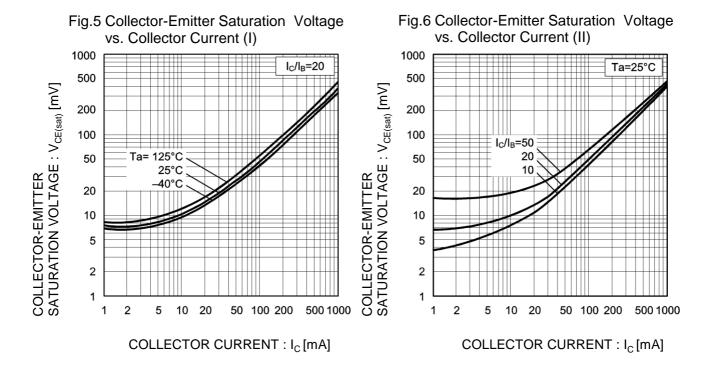
1000

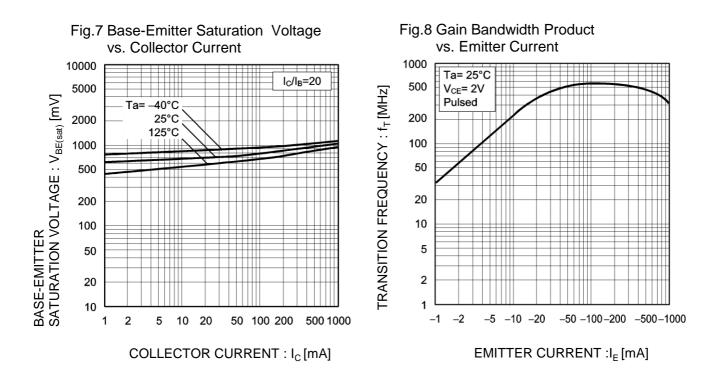
Fig.4 DC Current Gain vs. Collector Current(II)



COLLECTOR CURRENT : I_C [mA]

●Electrical characteristic curves(Ta = 25°C)

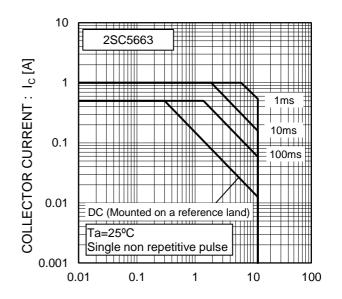




●Electrical characteristic curves(Ta = 25°C)

Fig.9 Emitter input capacitance vs. **Emitter-Base Voltage** Collector output capacitance vs. Collector-Base Voltage 1000 COLLECTOR OUTPUT CAPACITANCE: Cob [pF] Ta= 25°C 500 f=1MHz I_E=0A EMITTER INPUT CAPACITANCE: Cib [pF] 200 100 50 C_{ib} 20 C_{ob} 10 5 2

Fig.10 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE: V_{CE} [V]

Fig.11 Safe Operating Area

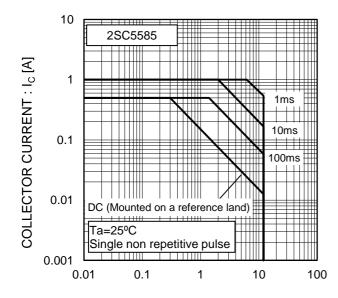
0.5

5 10 20

COLLECTOR - BASE VOLTAGE : V_{CB} [V] EMITTER - BASE VOLTAGE : V_{EB} [V]

50 100

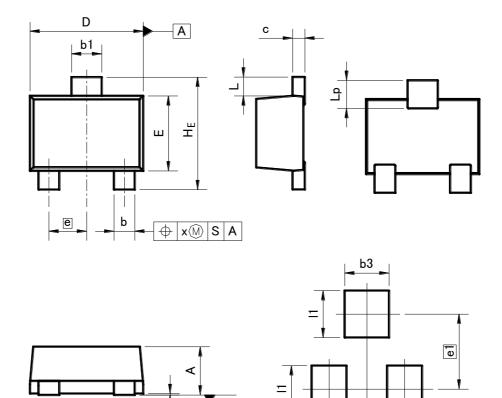
0.1 0.2



COLLECTOR TO EMITTER VOLTAGE: V_{CE}[V]

●Dimensions (Unit:mm)

VMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

b2

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.45	0.55	0.018	0.022	
A1	0.00	0.10	0.000	0.004	
b	0.17	0.27	0.007	0.011	
b1	0.27	0.37	0.011	0.015	
С	0.08	0.18	0.003	0.007	
D	1.10	1.30	0.043	0.051	
E	0.70	0.90	0.028	0.035	
е	0.	0.40		02	
HE	1.10	1.30	0.043	0.051	
Ĺ	0.10	0.30	0.004	0.012	
Lp	0.20	0.40	0.008	0.016	
х	_	0.10	_	0.004	

F

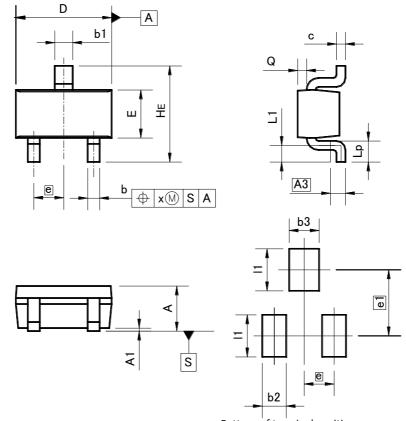
S

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	ı	0.37	_	0.015	
b3	_	0.47	_	0.019	
e1	0.80		0.0	31	
l1	-	0.50	_	0.020	

Dimension in mm / inches

●Dimensions (Unit:mm)

EMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.60	0.80	0.024	0.031	
A1	0.00	0.10	0.000	0.004	
A3	0.:	25	0.0	10	
b	0.15	0.30	0.006	0.012	
b1	0.25	0.40	0.010	0.016	
С	0.10	0.20	0.004	0.008	
D	1.50	1.70	0.059	0.067	
Е	0.70	0.90	0.028	0.035	
е	0.	50	0.0	20	
HE	1.40	1.80	0.055	0.071	
L1	0.10	_	0.004	ı	
Lp	0.15	_	0.006		
Q	0.05	0.25	0.002	0.010	
х	_	0.10	_	0.004	

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	_	0.40	_	0.016	
b3	_	0.50	_	0.020	
e1	1.10		0.0	43	
11	_	0.70	_	0.028	

Dimension in mm / inches

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